

Atsushi Ogura

List of Publications by Year in descending order

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308
papers

3,240
citations

218677

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h-index

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docs citations

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times ranked

2591
citing authors

#	ARTICLE	IF	CITATIONS
1	Malignant Features in Pretreatment Metastatic Lateral Lymph Nodes in Locally Advanced Low Rectal Cancer Predict Distant Metastases. <i>Annals of Surgical Oncology</i> , 2022, 29, 1194-1203.	1.5	9
2	ASO Visual Abstract: Malignant Features in Pretreatment Metastatic Lateral Lymph Nodes in Locally Advanced Low Rectal Cancer Predict Distant Metastases. <i>Annals of Surgical Oncology</i> , 2022, 29, 1206-1207.	1.5	1
3	Minimum radial margin in pelvic exenteration for locally advanced or recurrent rectal cancer. <i>European Journal of Surgical Oncology</i> , 2022, 48, 2502-2508.	1.0	2
4	Laparoscopic surgery for sigmoid colon cancer with complicated communication between the superior and inferior mesenteric arteries. <i>Asian Journal of Endoscopic Surgery</i> , 2021, 14, 267-270.	0.9	1
5	Free-to-bound emission from interstitial carbon and oxygen defects (C_{i} O_{i}) in electron-irradiated Si. <i>Applied Physics Express</i> , 2021, 14, 011006.	2.4	0
6	Comparison of characteristics of thin-film transistor with $In_{2}O_{3}$ and carbon-doped $In_{2}O_{3}$ channels by atomic layer deposition and post-metallization annealing in O_{3} . <i>Japanese Journal of Applied Physics</i> , 2021, 60, 030903.	1.5	6
7	Thermal conductivity and inelastic X-ray scattering measurements on SiGeSn polycrystalline alloy. <i>Japanese Journal of Applied Physics</i> , 2021, 60, SB8F11.	1.5	5
8	Simulation study on lateral minority carrier transport in the surface inversion layer of the p-aSi:H/i-aSi:H/cSi heterojunction solar cell. <i>Japanese Journal of Applied Physics</i> , 2021, 60, 026503.	1.5	2
9	Influence of adsorbed oxygen concentration on characteristics of carbon-doped indium oxide thin-film transistors under bias stress. <i>Japanese Journal of Applied Physics</i> , 2021, 60, SCCM01.	1.5	3
10	Effects of $Zn_{x}Mn_{1-x}S$ buffer layer on nonpolar AlN growth on Si (100) substrate. <i>Japanese Journal of Applied Physics</i> , 2021, 60, SCCG02.	1.5	0
11	Dependency of a localized phonon mode intensity on compositional cluster size in SiGe alloys. <i>AIP Advances</i> , 2021, 11, 075017.	1.3	3
12	Local recurrences in western low rectal cancer patients treated with or without lateral lymph node dissection after neoadjuvant (chemo)radiotherapy: An international multi-centre comparative study. <i>European Journal of Surgical Oncology</i> , 2021, 47, 2441-2449.	1.0	21
13	Atomic mass dependency of a localized phonon mode in SiGe alloys. <i>AIP Advances</i> , 2021, 11, .	1.3	8
14	Temperature and polarity dependence of electrical properties of ZnO film on pyroelectric LiNbO ₃ single crystal. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SIIG11.	1.5	0
15	Phonon dispersion of bulk Ge-rich SiGe: inelastic X-ray scattering studies. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 061003.	1.5	4
16	Thermal conductivity characteristics in polycrystalline silicon with different average sizes of grain and nanostructures in the grains by UV Raman spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 075501.	1.5	4
17	Quantification of Ge fraction using local vibrational modes in Raman spectra of silicon germanium by oil-immersion Raman spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 075502.	1.5	0
18	Stress evaluation induced by wiggling silicon nitride fine pattern using Raman spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SIIF03.	1.5	1

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19	Band alignment at non-polar AlN/MnS interface investigated by hard X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2020, 59, S11G07.	1.5	2
20	Superior subthreshold characteristics of gate-all-around p-type junctionless poly-Si nanowire transistor with ideal subthreshold slope. Japanese Journal of Applied Physics, 2020, 59, 070908.	1.5	7
21	Width dependence of drain current and carrier mobility in gate-all-around multi-channel polycrystalline silicon nanowire transistors with 10 nm width scale. Japanese Journal of Applied Physics, 2020, 59, 021004.	1.5	1
22	Cranial-first approach for safe laparoscopic surgery in right-sided colon cancer. Techniques in Coloproctology, 2020, 24, 489-490.	1.8	0
23	Anisotropic biaxial stress evaluation in metal-organic chemical vapor deposition grown Ge1-Sn mesa structure by oil-immersion Raman spectroscopy. Thin Solid Films, 2020, 697, 137797.	1.8	2
24	Surface inversion layer effective minority carrier mobility as one of the measures of surface quality of the p-aSi:H/i-aSi:H/cSi heterojunction solar cell. Japanese Journal of Applied Physics, 2020, 59, SGGF06.	1.5	1
25	Evaluation of plasma induced defects on silicon substrate by solar cell fabrication process. Japanese Journal of Applied Physics, 2020, 59, 071003.	1.5	7
26	Anomalous excitation-power dependence of band-edge emission in Si involving radiation-induced defects. Japanese Journal of Applied Physics, 2020, 59, 106502.	1.5	4
27	Detection limit of carbon concentration measurement in Si for photoluminescence method after electron irradiation. Japanese Journal of Applied Physics, 2020, 59, 126501.	1.5	3
28	Origin of carrier lifetime degradation in floating-zone silicon during a high-temperature process for insulated gate bipolar transistor. Japanese Journal of Applied Physics, 2020, 59, 115503.	1.5	0
29	Evaluation of thermal conductivity characteristics in Si nanowire covered with oxide by UV Raman spectroscopy. Japanese Journal of Applied Physics, 2019, 58, SDDF04.	1.5	1
30	Effects of substrate self-bias and nitrogen flow rate on non-polar AlN film growth by reactive sputtering. Japanese Journal of Applied Physics, 2019, 58, SDDG07.	1.5	8
31	3300V Scaled IGBTs Driven by 5V Gate Voltage. , 2019, , .		6
32	Effects of surface recombination and excitation power on quantitative analysis of carbon in Si using room-temperature photoluminescence after electron irradiation. Japanese Journal of Applied Physics, 2019, 58, 076502.	1.5	4
33	Improvement in ferroelectricity of HfxZr1-xO2 thin films using top- and bottom-ZrO2 nucleation layers. APL Materials, 2019, 7, .	5.1	46
34	Lateral Nodal Features on Restaging Magnetic Resonance Imaging Associated With Lateral Local Recurrence in Low Rectal Cancer After Neoadjuvant Chemoradiotherapy or Radiotherapy. JAMA Surgery, 2019, 154, e192172.	4.3	141
35	Suppression of threshold voltage shift on In-Si-O-C Thin-Film Transistor with an Al2O3 Passivation Layer under Negative and Positive Gate-Bias Stress. , 2019, , .		0
36	Effect of additives in electrode paste of p-type crystalline Si solar cells on potential-induced degradation. Solar Energy, 2019, 188, 1292-1297.	6.1	10

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37	Ferroelectricity of Hf _x Zr _{1-x} O ₂ thin films fabricated by 300°C low temperature process with plasma-enhanced atomic layer deposition. <i>Microelectronic Engineering</i> , 2019, 215, 111013.	2.4	55
38	Cranial-first approach for laparoscopic surgery with splenic flexure mobilization. <i>Techniques in Coloproctology</i> , 2019, 23, 693-694.	1.8	4
39	Lifetime Degradation by Oxygen Precipitation Combined with Metal Contamination in Czochralski Silicon for Solar Cells. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q72-Q75.	1.8	5
40	Crystal growth of a MnS buffer layer for non-polar AlN on Si (100) deposited by radio frequency magnetron sputtering. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SBBK03.	1.5	3
41	Evaluations of minority carrier lifetime in floating zone Si affected by Si insulated gate bipolar transistor processes. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SBBD07.	1.5	1
42	Effect of oxygen precipitation through annealing process on lifetime degradation by Czochralski-Si crystal growth conditions. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SBBF02.	1.5	6
43	Neoadjuvant (Chemo)radiotherapy With Total Mesorectal Excision Only Is Not Sufficient to Prevent Lateral Local Recurrence in Enlarged Nodes: Results of the Multicenter Lateral Node Study of Patients With Low cT3/4 Rectal Cancer. <i>Journal of Clinical Oncology</i> , 2019, 37, 33-43.	1.6	308
44	Evaluation of ITO/a-Si Interface Fabricated by RPD Technique. , 2019, , .		0
45	Anisotropic Biaxial Strain Evaluation in Carbon-Doped Silicon Using Water-Immersion Raman Spectroscopy. <i>ECS Transactions</i> , 2019, 92, 33-39.	0.5	2
46	Ultra-Thin Lightweight Bendable Crystalline Si Solar Cells for Solar Vehicles. , 2019, , .		1
47	Effect of post-deposition annealing on electrical properties and structures of aluminum oxide passivation film on a crystalline silicon substrate. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 125502.	1.5	1
48	Complete Resection without Any Ostomies by Laparoscopic Extended Surgery for Locally Advanced T4 Sigmoid Colon Cancer Invading the Urinary Bladder and Ureter. <i>Case Reports in Surgery</i> , 2019, 2019, 1-5.	0.4	1
49	Effects of damages induced by indium-tin-oxide reactive plasma deposition on minority carrier lifetime in silicon crystal. <i>AIP Advances</i> , 2019, 9, .	1.3	8
50	Characteristics of Oxide TFT Using Carbon-Doped In ₂ O ₃ Thin Film Fabricated by Low-Temperature ALD Using Ethylcyclopentadienyl Indium (In-EtCp) and H ₂ O & O ₃ . <i>ECS Transactions</i> , 2019, 92, 3-13.	0.5	17
51	Fabrication of MoS ₂ (1-x)Te _x via Sulfurization using (t-C ₄ H ₉) ₂ S ₂ and its Physical Structure Evaluation. , 2019, , .		0
52	Cranial-first approach of laparoscopic left colectomy for T4 descending colon cancer invading the Gerota's fascia. <i>Surgical Case Reports</i> , 2019, 5, 159.	0.6	0
53	Low-Carrier-Density Sputtered MoS ₂ Film by Vapor-Phase Sulfurization. <i>Journal of Electronic Materials</i> , 2018, 47, 3497-3501.	2.2	36
54	Improved leakage current properties of ZrO ₂ /(Ta/Nb) _x Al ₂ O ₃ /ZrO ₂ nanolaminate insulating stacks for dynamic random access memory capacitors. <i>Thin Solid Films</i> , 2018, 655, 48-53.	1.8	16

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55	Pattern of programmed cell death-ligand 1 expression and CD8-positive T-cell infiltration before and after chemoradiotherapy in rectal cancer. <i>European Journal of Cancer</i> , 2018, 91, 11-20.	2.8	55
56	Chemical Synthesis of Multilayered Nanostructured Perovskite Thin Films with Dielectric Features for Electric Capacitors. <i>ACS Applied Nano Materials</i> , 2018, 1, 915-921.	5.0	11
57	Origin of room-temperature photoluminescence around C-line in electron-irradiated Si and its applicability for quantification of carbon. <i>Applied Physics Express</i> , 2018, 11, 041301.	2.4	9
58	Study of Sn and Mg doping effects on TiO ₂ /Ge stack structure by combinatorial synthesis. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 04FJ04.	1.5	0
59	Distribution of light-element impurities in Si crystals grown by seed-casting method. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 08RB19.	1.5	1
60	Determination of C concentration in P-doped n-type Czochralski-grown Si crystals by liquid N temperature photoluminescence after electron irradiation. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 08RB06.	1.5	5
61	Evaluation of lifetime degradation caused by oxygen precipitation combined with metal contamination in Cz-Si for solar cells. , 2018, , .		0
62	Machine Learning for Automated Etch Pit Counting on As-sliced Surface of Multicrystalline Silicon. , 2018, , .		1
63	Potential of Chemical Rounding for the Performance Enhancement of a Monolithic Perovskite/Bifacial N-PERT Si Tandem Cell. , 2018, , .		0
64	Evaluation of Anisotropic Three-Dimensional Strain Relaxation in Stripe-Shaped Ge _{1-x} Sn _x Mesa Structure. <i>ECS Transactions</i> , 2018, 86, 329-336.	0.5	3
65	Reliability of Al ₂ O ₃ /In-Si-O-C Thin-Film Transistors with an Al ₂ O ₃ Passivation Layer under Gate-Bias Stress. <i>ECS Transactions</i> , 2018, 86, 135-145.	0.5	4
66	Ferroelectricity of Hf _x Zr _{1-x} O ₂ Thin Films Fabricated Using TiN Stressor and ZrO ₂ Nucleation Techniques. <i>ECS Transactions</i> , 2018, 86, 31-38.	0.5	9
67	Determination of Phonon Deformation Potentials in Carbon-Doped Silicon. <i>ECS Transactions</i> , 2018, 86, 419-425.	0.5	2
68	Evaluation of ITO/a-Si interface properties by hard X-ray photoemission spectroscopy. , 2018, , .		0
69	Effect of ITO Capping Layer on Interface Workfunction of MoO ₃ /ITO/MoO ₃ /SiO ₂ /Si Contacts. , 2018, , .		0
70	Study on chemical bonding states at electrode-silicon interface fabricated with fire-through control paste. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 08RB23.	1.5	1
71	Sputter-Deposited-MoS ₂ MISFETs With Top-Gate and Al ₂ O ₃ Passivation Under Low Thermal Budget for Large Area Integration. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 1246-1252.	2.1	10
72	(Invited) High-Sn Concentration MOCVD-Grown Strained GeSn Thin Films Evaluated Using HAXPES and XRD Base on Synchrotron Technique. <i>ECS Transactions</i> , 2018, 86, 411-418.	0.5	1

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73	Evaluation of Laterally Graded Silicon Germanium Wires for Thermoelectric Devices Fabricated by Rapid Melting Growth. ECS Transactions, 2018, 86, 87-93.	0.5	8
74	Strain Evaluation of Laser-Annealed SiGe Thin Layers. ECS Transactions, 2018, 86, 59-65.	0.5	2
75	Investigation on Mo _{1-x} W _x S ₂ fabricated by co-sputtering and post-deposition sulfurization with (C ₄ H ₉) ₂ S ₂ . Japanese Journal of Applied Physics, 2018, 57, 06HB04.	1.5	2
76	Determination of phonon deformation potentials and strain-shift coefficients in Ge-rich Si _{1-x} Ge _x using bulk Ge-rich Si _{1-x} Ge _x crystals and oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 106601.	1.5	12
77	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, 061206.	1.2	5
78	Evaluation of oxygen precipitation behavior in n-type Czochralski-Si for photovoltaic by infrared tomography: Effects of carbon concentration and annealing process conditions. Japanese Journal of Applied Physics, 2018, 57, 08RB01.	1.5	1
79	Skeletal muscle loss is an independent negative prognostic factor in patients with advanced lower rectal cancer treated with neoadjuvant chemoradiotherapy. PLoS ONE, 2018, 13, e0195406.	2.5	46
80	Potential of chemical rounding for the performance enhancement of pyramid textured p-type emitters and bifacial n-PERT Si cells. Current Applied Physics, 2018, 18, 1268-1274.	2.4	6
81	Chip-Level-Integrated n-MISFETs with Sputter-Deposited-MoS ₂ Thin Channel Passivated by Al ₂ O ₃ Film and TiN Top Gate. , 2018, , .		0
82	Control of dipole properties in high-k and SiO ₂ stacks on Si substrates with tricolor superstructure. Applied Physics Letters, 2018, 113, .	3.3	10
83	Evaluation of Anisotropic Biaxial Stress Induced Around Trench Gate of Si Power Transistor Using Water-Immersion Raman Spectroscopy. Journal of Electronic Materials, 2018, 47, 5050-5055.	2.2	2
84	Determination of Low C Concentration in Czochralski-Grown Si for Solar Cell Applications by Liquid-N-Temperature Photoluminescence After Electron Irradiation. Journal of Electronic Materials, 2018, 47, 5056-5060.	2.2	3
85	Endoscopic criteria to evaluate tumor response of rectal cancer to neoadjuvant chemoradiotherapy using magnifying chromoendoscopy. European Journal of Surgical Oncology, 2018, 44, 1247-1253.	1.0	12
86	Evaluation of saw damage using diamond-coated wire in crystalline silicon solar cells by photoluminescence imaging. Japanese Journal of Applied Physics, 2018, 57, 055702.	1.5	5
87	Miniaturized planar Si-nanowire micro-thermoelectric generator using exuded thermal field for power generation. Science and Technology of Advanced Materials, 2018, 19, 443-453.	6.1	43
88	Effects of particle size of aluminum powder in silver/aluminum paste on n-type solar cells. AIMS Materials Science, 2018, 5, 614-623.	1.4	3
89	The significance of extended lymphadenectomy for colorectal cancer with isolated synchronous extraregional lymph node metastasis. Asian Journal of Surgery, 2017, 40, 254-261.	0.4	31
90	Role of H ₂ supply for Sn incorporations in MOCVD Ge _{1-x} Sn _x epitaxial growth. Journal of Crystal Growth, 2017, 468, 605-609.	1.5	6

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91	Effects of thermal budget in n-type bifacial solar cell fabrication processes on effective lifetime of crystalline silicon. AIP Advances, 2017, 7, .	1.3	12
92	Quantitative relationship between sputter-deposited-MoS ₂ properties and underlying-SiO ₂ surface roughness. Applied Physics Express, 2017, 10, 041202.	2.4	26
93	Investigation of the static electric field effect of strontium silicate layers on silicon substrates. Journal of Applied Physics, 2017, 121, 225302.	2.5	3
94	Local anisotropic strain evaluation in thin Ge epitaxial film using SiGe stressor template grown on Ge substrate by selective ion implantation. Japanese Journal of Applied Physics, 2017, 56, 110313.	1.5	7
95	Enhanced nickelidation rate in silicon nanowires with interfacial lattice disorder. Journal of Applied Physics, 2017, 122, .	2.5	6
96	The electrical losses induced by silver paste in n-type silicon solar cells. Japanese Journal of Applied Physics, 2017, 56, 102302.	1.5	3
97	Quantification of C in Si by photoluminescence at liquid N temperature after electron irradiation. Applied Physics Express, 2017, 10, 046602.	2.4	12
98	Improvement in ferroelectricity of Hf _x Zr _{1-x} O ₂ thin films using ZrO ₂ seed layer. Applied Physics Express, 2017, 10, 081501.	2.4	63
99	Characterization of Glass Frit in Conductive Paste for N-Type Crystalline Silicon Solar Cells. IEEE Journal of Photovoltaics, 2017, 7, 1313-1318.	2.5	7
100	Photoluminescence due to early stage of oxygen precipitation in multicrystalline Si for solar cells. Japanese Journal of Applied Physics, 2017, 56, 070308.	1.5	2
101	Band gap-tuned MoS ₂ (1-x)Te _x thin films synthesized by a hybrid Co-sputtering and post-deposition tellurization annealing process. Journal of Materials Research, 2017, 32, 3021-3028.	2.6	6
102	Improvement of smooth surface of RuO ₂ bottom electrode on Al ₂ O ₃ buffer layer and characteristics of RuO ₂ /TiO ₂ /Al ₂ O ₃ /TiO ₂ /RuO ₂ capacitors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	2.1	8
103	Probing spatial heterogeneity in silicon thin films by Raman spectroscopy. Scientific Reports, 2017, 7, 16549.	3.3	3
104	Determination of low carbon concentration in Czochralski-grown Si crystals for solar cells by luminescence activation using electron irradiation. Japanese Journal of Applied Physics, 2017, 56, 070305.	1.5	9
105	Feasibility of Laparoscopic Total Mesorectal Excision with Extended Lateral Pelvic Lymph Node Dissection for Advanced Lower Rectal Cancer after Preoperative Chemoradiotherapy. World Journal of Surgery, 2017, 41, 868-875.	1.6	62
106	Does the depth of mesorectal invasion have prognostic significance in patients with ypT3 lower rectal cancer treated with preoperative chemoradiotherapy?. International Journal of Colorectal Disease, 2017, 32, 349-356.	2.2	2
107	Characteristics variability of gate-all-around polycrystalline silicon nanowire transistors with width of 10nm scale. , 2017, , .		0
108	Pattern-dependent anisotropic stress evaluation in SiGe epitaxially grown on a Si substrate with selective Ar ⁺ ion implantation using oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2017, 56, 051301.	1.5	1

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109	Evaluation of controlled strain in silicon nanowire by UV Raman spectroscopy. Japanese Journal of Applied Physics, 2017, 56, 06GG10.	1.5	4
110	Effect of Y and Mn doping into rutile type TiO ₂ /Ge stack structure by combinatorial synthesis. Japanese Journal of Applied Physics, 2017, 56, 06GF11.	1.5	3
111	Properties of single-layer MoS ₂ film fabricated by combination of sputtering deposition and post deposition sulfurization annealing using (t-C ₄ H ₉) ₂ S ₂ . Japanese Journal of Applied Physics, 2016, 55, 06GF01.	1.5	16
112	Investigation of new stacking surface passivation structures with interfacial tuning layers on p-type crystalline silicon. Japanese Journal of Applied Physics, 2016, 55, 04ES03.	1.5	0
113	Thin-film growth of (110) rutile TiO ₂ on (100) Ge substrate by pulsed laser deposition. Japanese Journal of Applied Physics, 2016, 55, 06GG06.	1.5	2
114	Improving crystalline quality of sputtering-deposited MoS ₂ thin film by postdeposition sulfurization annealing using (t-C ₄ H ₉) ₂ S ₂ . Japanese Journal of Applied Physics, 2016, 55, 04EJ07.	1.5	26
115	Anisotropic strain evaluation induced in group IV materials using liquid-immersion Raman spectroscopy. , 2016, , .		0
116	Positive and negative dipole layer formation at high-k/SiO ₂ interfaces simulated by classical molecular dynamics. Japanese Journal of Applied Physics, 2016, 55, 04EB03.	1.5	25
117	Minority Carrier Recombination Properties of Crystalline Defect on Silicon Surface Induced by Plasma Enhanced Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2016, 5, Q253-Q256.	1.8	14
118	Correlation between chemical-bonding states and fixed-charge states of Sr-silicate film on Si(100) substrate. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	4
119	Effects of Aluminum in Metallization Paste on the Electrical Losses in Bifacial N-type Crystalline Silicon Solar Cells. Energy Procedia, 2016, 98, 106-114.	1.8	14
120	Effect of glass frit in metallization paste on the electrical losses in bifacial N-type crystalline silicon solar cells. , 2016, , .		0
121	Detection of short range order in SiO ₂ thin-films by grazing-incidence wide and small-angle X-ray scattering. Journal of Applied Physics, 2016, 119, 154103.	2.5	1
122	A study on the evaluation method of glass frit paste for crystalline silicon solar cells. , 2016, , .		3
123	Fabrication and performance analysis of a mechanical stack InGaP/GaAs//Si solar cell. , 2016, , .		4
124	Origin of additional broad peaks in Raman spectra from thin germanium-rich silicon-germanium films. Applied Physics Express, 2016, 9, 071301.	2.4	7
125	Large Scale Uniformity of Sputtering Deposited Single- and Few-Layer MoS ₂ Investigated by XPS Multipoint Measurements and Histogram Analysis of Optical Contrast. ECS Journal of Solid State Science and Technology, 2016, 5, Q3012-Q3015.	1.8	12
126	Biaxial stress evaluation in GeSn film epitaxially grown on Ge substrate by oil-immersion Raman spectroscopy. Japanese Journal of Applied Physics, 2016, 55, 091301.	1.5	18

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127	Development of Interatomic Potential of Group IV Alloy Semiconductors for Lattice Dynamics Simulation. ECS Transactions, 2016, 75, 785-794.	0.5	2
128	Patient-centered outcomes to decide treatment strategy for patients with low rectal cancer. Journal of Surgical Oncology, 2016, 114, 630-636.	1.7	14
129	Oxygen precipitates distributed around random grain boundaries in a cast-grown multicrystalline silicon crystal. Japanese Journal of Applied Physics, 2016, 55, 041302.	1.5	4
130	Electrically active light-element complexes in silicon crystals grown by cast method. Japanese Journal of Applied Physics, 2016, 55, 095502.	1.5	1
131	Room temperature formation of Hf-silicate layer by pulsed laser deposition with Hf-Si-O ternary reaction control. AIP Advances, 2016, 6, 105303.	1.3	0
132	Safety of Laparoscopic Pelvic Exenteration with Urinary Diversion for Colorectal Malignancies. World Journal of Surgery, 2016, 40, 1236-1243.	1.6	27
133	Examination of phonon deformation potentials for accurate strain measurements in silicon-germanium alloys with the whole composition range by Raman spectroscopy. Japanese Journal of Applied Physics, 2016, 55, 026602.	1.5	8
134	Recurrent colorectal cancer after endoscopic resection when additional surgery was recommended. World Journal of Gastroenterology, 2016, 22, 2336-2341.	3.3	5
135	Multi-layered MoS ₂ film formed by high-temperature sputtering for enhancement-mode nMOSFETs. Japanese Journal of Applied Physics, 2015, 54, 04DN08.	1.5	53
136	Influence of Al ₂ O ₃ layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	6
137	Plasma-enhanced chemical-vapor deposition of silicon nitride film for high resistance to potential-induced degradation. Japanese Journal of Applied Physics, 2015, 54, 08KD12.	1.5	16
138	Photoluminescence due to impurity-cluster-bound exciton in highly doped and highly compensated Si. Japanese Journal of Applied Physics, 2015, 54, 111304.	1.5	5
139	Photoluminescence characterization of Si crystals for microelectronic and photovoltaic devices. , 2015, , .		0
140	Structural Analyses of Thin SiO ₂ Films Formed by Thermal Oxidation of Atomically Flat Si Surface by Using Synchrotron Radiation X-Ray Characterization. ECS Journal of Solid State Science and Technology, 2015, 4, N96-N98.	1.8	5
141	Advantage in solar cell efficiency of high-quality seed cast mono Si ingot. Applied Physics Express, 2015, 8, 062301.	2.4	17
142	Surface passivation of crystalline silicon by sputtered AlO _x /AlN _x stacks toward low-cost high-efficiency silicon solar cells. Japanese Journal of Applied Physics, 2015, 54, 08KD18.	1.5	4
143	Relationship between passivation properties and band alignment in O ₃ -based atomic-layer-deposited AlO _x crystalline Si for photovoltaic applications. Japanese Journal of Applied Physics, 2015, 54, 08KD19.	1.5	6
144	Passivation properties of aluminum oxide films deposited by mist chemical vapor deposition for solar cell applications. Japanese Journal of Applied Physics, 2015, 54, 08KD25.	1.5	2

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145	Effects of stacking passivation structure with interface tuning layer for crystalline Si solar cell applications. , 2015, , .		0
146	Endoscopic evaluation of clinical response after preoperative chemoradiotherapy for lower rectal cancer: the significance of endoscopic complete response. International Journal of Colorectal Disease, 2015, 30, 367-373.	2.2	12
147	Investigation of dislocations in Nb-doped SrTiO ₃ by electron-beam-induced current and transmission electron microscopy. Applied Physics Letters, 2015, 106, 102109.	3.3	10
148	Ge incorporated epitaxy of (110) rutile TiO ₂ on (100) Ge single crystal at low temperature by pulsed laser deposition. Thin Solid Films, 2015, 591, 105-110.	1.8	8
149	Oil-Immersion Raman Spectroscopy for c-Plane GaN on Si and Al ₂ O ₃ Substrates. ECS Transactions, 2015, 66, 119-126.	0.5	1
150	Growth of Ge Homoepitaxial Films by Metal-Organic Chemical Vapor Deposition Using t-C ₄ H ₉ GeH ₃ . ECS Journal of Solid State Science and Technology, 2015, 4, P152-P154.	1.8	9
151	X-ray evaluation of electronic and chemical properties and film structures in SiN passivation layer on crystalline Si solar cells. Japanese Journal of Applied Physics, 2015, 54, 08KD14.	1.5	5
152	Nanocrystalline-Si-dot multi-layers fabrication by chemical vapor deposition with H-plasma surface treatment and evaluation of structure and quantum confinement effects. AIP Advances, 2014, 4, 017133.	1.3	2
153	Evaluation of the Silicon Ingot With Addition of SiCl ₄ in Atmosphere During Unidirectional Solidification. IEEE Journal of Photovoltaics, 2014, 4, 581-584.	2.5	1
154	Molecular dynamics study on the formation of dipole layer at high-k/SiO ₂ interfaces. Japanese Journal of Applied Physics, 2014, 53, 08LB02.	1.5	7
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